

**Enterprise PCIe U.2/U.3
(PS5020-P1) SK hynix V6 eTLC
Specification
EPW9970 EPM9970
V 1.3**



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REVISION HISTORY

Revision	Draft Date	History	Author
1.3	2022-11-04	First release	CC Yeh

This specification is based on firmware revision of EKxxxxxx -series and is subject to change without notice. Any deviation on following firmware revisions will not be updated unless the deviation is more than 5%.

PRODUCT OVERVIEW

EPM9970 EPW9970

- Capacities
 - OP=7%: 1920, 3840, 7680, 15360, 30720 GB
 - OP=28%: 800, 1600, 3200, 6400, 12800, 25600 GB
- Form Factor
 - U.2/U.3 15mm
 - U.2/U.3 7mm
- PCIe Interface
 - PCIe Gen4x4
 - Single Port x4 lanes
 - PCIe AER (Advanced Error Reporting)
- Performance
 - Maximum Sequential Read/Write
 - Maximum Random Read/Write
 - Latency (Sustained workload)
 - IOPS Consistency
 - QoS (Quality of Service, 99% and 99.999%)¹
- Power Consumption²
 - Active Power: 25 W
 - Inrush Current: 1.5A
 - Idle Power: 6.0 W / 8.0 W (16T)
- DWPD
 - 1DWPD – 1920, 3840, 7680, 15360, 30720 GB
 - 3DWPD – 800, 1600, 3200, 6400, 12800, 25600 GB
- TBW³
 - 800GB SSD – 4380 TB
 - 1600GB SSD – 8760 TB
 - 1920GB SSD – 3504 TB
 - 3200GB SSD – 17520 TB
 - 3840GB SSD – 7008 TB
 - 6400GB SSD – 35040 TB
 - 7680GB SSD – 14016 TB
 - 12800GB SSD – 70080 TB
 - 15360GB SSD – 28032 TB
 - 25600GB SSD – TBD
 - 30720GB SSD – TBD
- MTBF⁴
- UBER
- Advanced Flash Management
 - ECC
 - Static and Dynamic Wear Leveling
 - Bad Block Management
 - Deallocate (TRIM) Command
 - SMART
 - Over-Provision
 - Firmware Upgrade
- Temperature Range
 - Operation: 0°C ~ 70°C with specified airflow
 - Storage: -40°C ~ 85°C
- RoHS compliant
- Enterprise Features Support List:
 - Namespace
 - Metadata Protection Thermal throttling
 - Power Loss Protection
- Hardware AES-XTS 256-bit Encryption
- Support SMBus
- Support NVMe-MI (Management Interface)
- Data Retention – 3 months
- Physical Dimension:
 - U.2/U.3 15mm 100(L)x70(W)x15(H) mm³
 - U.2/U.3 7mm 100(L)x70(W)x7(H) mm³
- Compliance
 - PCIe Express Base 4.0
 - NVMe Express 1.4
 - NVMe Express Management Interface Rev 1.1

NOTES:

1. Please see “Performance to Quality of Service (QoS)” Chapter 2.5 and 1.1 for details.
2. Please see “Power Consumption” Chapter 4.2 for details.
3. Please see “TBW (Terabytes Written)” Chapter 3.2 for details.
4. MTBF is a prediction simulation based on Telcordia SR-332 model.

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1. INTRODUCTION

1.1. General Description

Phison’s PS5020-E20 (hereinafter referred as X1) U.2/U.3(15mm) Solid State Disk (SSD) delivers all the advantages of flash disk technology with PCIe Gen4 x4 interface, including being fully compliant with standard U.2/U.3 form factor, providing low power consumption compared to traditional hard drive and hot-swapping when removing/replacing/upgrading flash disks. X1 offers a wide range of capacities up to 15,360GB and its performance can reach up to 7000 MB/s (for sequential read) and 7000 MB/s (for sequential write) based on SK hynix V6 eTLC NAND flash with the DDR4. Moreover, the power consumption of U.2/X1 U.3(15mm) SSD is much lower than traditional hard drives, making it the best embedded solution for new platforms.

1.2. Controller Block Diagram

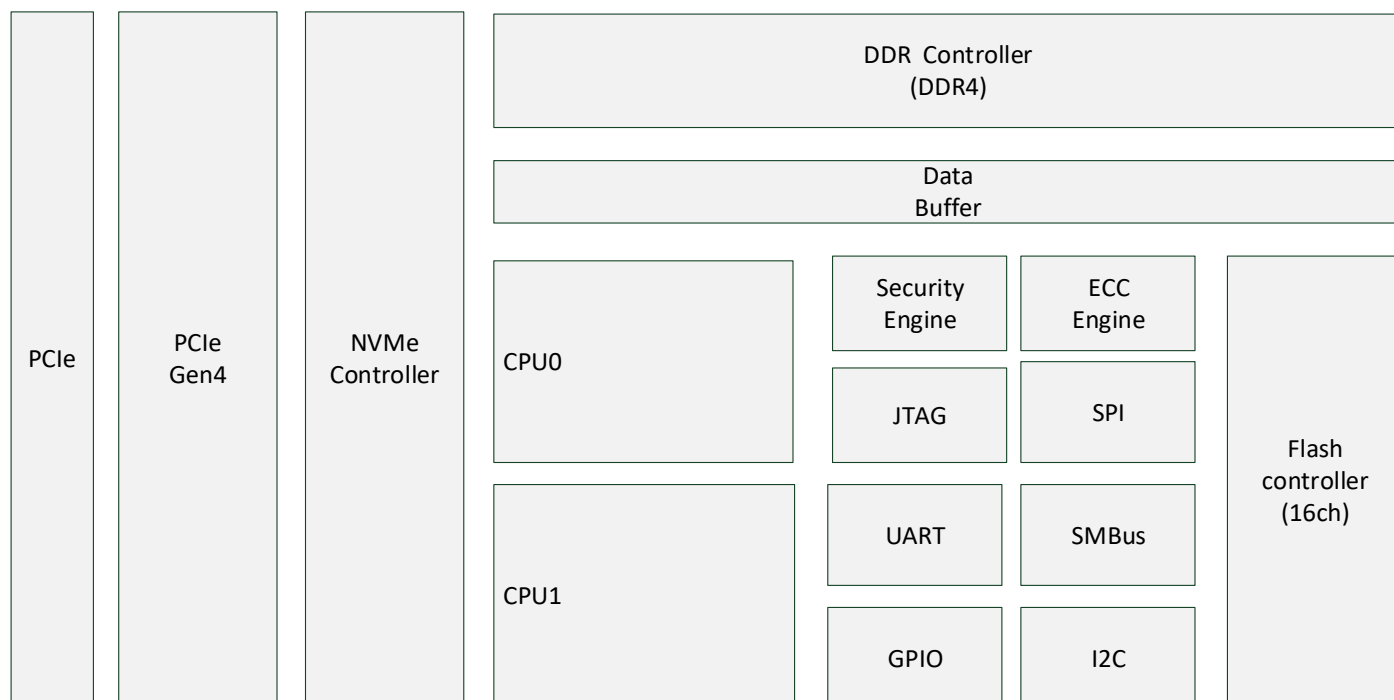


Figure 1-1 X1 U.3 PCIe SSD Controller Block Diagram

1.3. Product Block Diagram

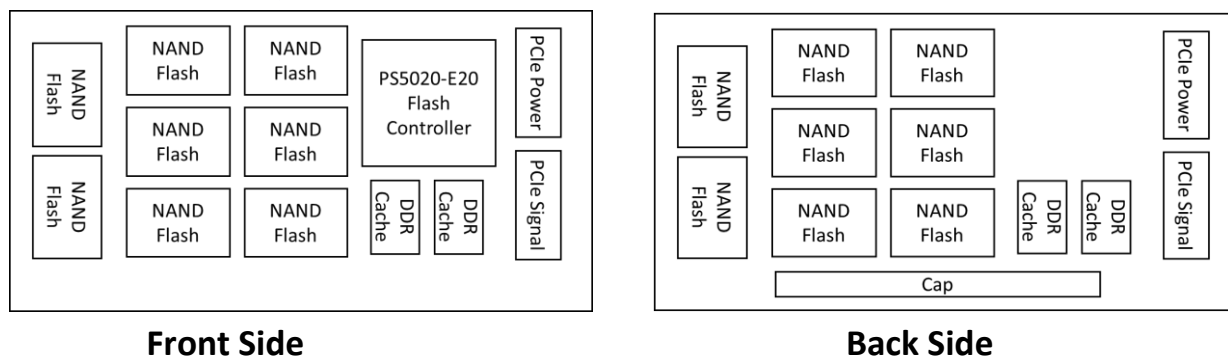


Figure 1-2 X1 U.3(15mm) PCIe SSD Product Block Diagram

1.4. Flash Management

1.4.1. Error Correction Code (ECC)

Flash memory cells will deteriorate with use, which might generate random bit errors in the stored data. Thus, X1 PCIe SSD applies the 445bit/4KB LDPC (Low Density Parity Check) of ECC algorithm, which can detect and correct errors occur during read process, ensure data been read correctly, as well as protect data from corruption.

1.4.2. Wear Leveling

NAND flash devices can only undergo a limited number of program/erase cycles, and in most cases, the flash media are not used evenly. If some areas get updated more frequently than others, the lifetime of the device would be reduced significantly. Thus, Wear Leveling is applied to extend the lifespan of NAND Flash by evenly distributing write and erase cycles across the media.

Phison provides advanced Wear Leveling algorithm, which can efficiently spread out the flash usage through the whole flash media area. Moreover, by implementing both dynamic and static Wear Leveling algorithms, the life expectancy of the NAND flash is greatly improved.

1.4.3. Bad Block Management

Bad blocks are blocks that do not function properly or contain more invalid bits causing stored data unstable, and their reliability is not guaranteed. Blocks that are identified and marked as bad by the manufacturer are referred to as “Early Bad Blocks”. Bad blocks that are developed during the lifespan of the flash are named “Later Bad Blocks”. Phison implements an efficient bad block management algorithm to detect the factory-produced bad blocks and manages bad blocks that appear with use. This practice prevents data being stored into bad blocks and further improves the data reliability.

1.4.4. TRIM

TRIM is a feature which helps improve the read/write performance and speed of solid-state drives (SSD). Unlike hard disk drives (HDD), SSDs are not able to overwrite existing data, so the available space gradually becomes smaller with each use. With the TRIM command, the operating system can inform the SSD which blocks of data are no longer in use and can be removed permanently. Thus, the SSD will perform the erase action, which prevents unused data from occupying blocks all the time.

1.4.5. SMART

SMART, an acronym for Self-Monitoring, Analysis and Reporting Technology, is an open standard that allows a disk drive to automatically detect its health and report potential failures. When a failure is recorded by SMART, users can

choose to replace the drive to prevent unexpected outage or data loss. Moreover, SMART can inform users of impending failures while there is still time to perform proactive actions, such as copy data to another device.

1.4.6. Over-Provision

Over Provisioning refers to the preserving additional area beyond user capacity in a SSD, which is not visible to users and cannot be used by them. With Over Provisioning, the performance and IOPS (Input/Output Operations per Second) are improved by providing the controller additional space to manage P/E cycles, which enhances the reliability and endurance as well. Moreover, the write amplification of the SSD becomes lower when the controller writes data to the flash.

1.4.7. Firmware Upgrade

Firmware can be considered as a set of instructions on how the device communicates with the host. Firmware will be upgradable when new features are added, compatibility issues are fixed, or read/write performance gets improved.

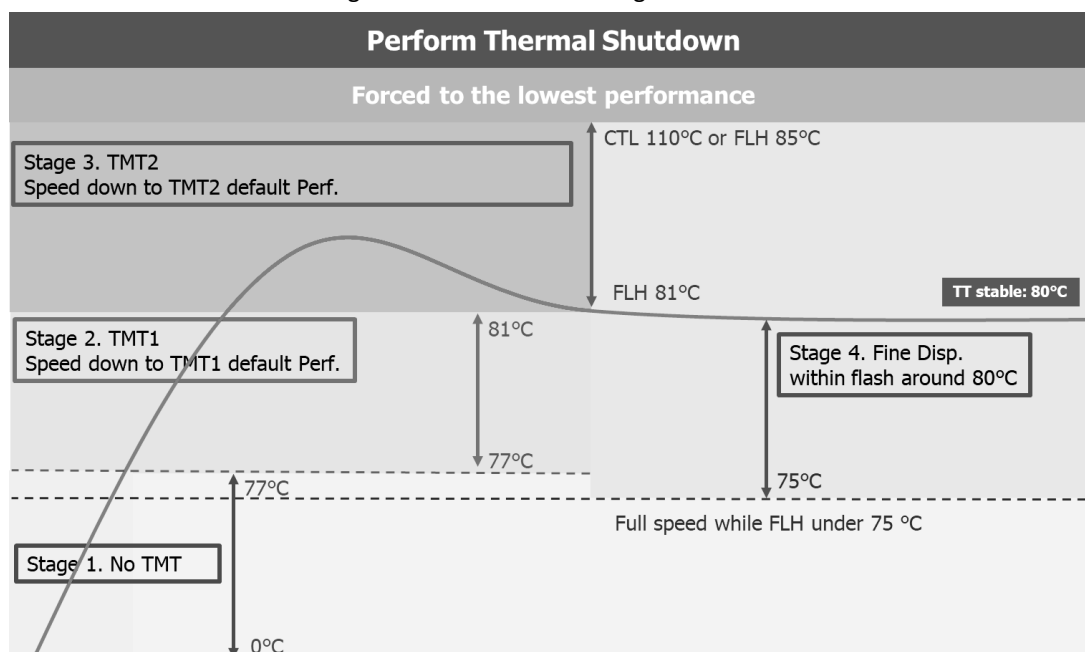
1.4.8. Thermal Throttling

The purpose of thermal throttling is to prevent any components in a SSD from over-heating during read and write operations. X1 is designed with multiple on-board thermal sensors and with their accuracy, firmware can apply different levels of throttling to achieve the purpose of protection efficiently and proactively via SMART reading.

Table 1-1 Thermal Throttling Mechanism

Item	Contents
Stage 1 No TMT	To monitor temperature every 1 secs, until flash temperature is over 77 °C. Clock frequency mode 0
Stage 2 TMT1	When flash temp reaches TMT1 (flash 77 °C), the drive will speed down to TMT1 performance(< 2000MB/s).
Stage 3 TMT2	When flash temp reaches TMT2 (flash 81 °C), the drive will speed down to TMT2 performance(< 450MB/s).
Stage 4 TT Stable	Enter TT Dynamic Mechanism (keep TMT1 state 60 sec or TMT2 state 15 sec) Once CTRL (+/- 2) or FLH (+/- 1) temp change: 3% increase or decline of full performance in TMT1 to TMT2 temp range(75~81°C) 3% increase or 9% decline of full performance in TMT2 to Protect temp range(81~85°C)
TMT Protect	When the controller is over 110°C or flash is over 85°C , the drive will be forced to perform at the lowest performance (< 50 MB/s)
TMT Fatal	Perform thermal shutdown process when controller T _J is 120°C.
Resume No TMT	While flash is cooled down to 75°C or below, the performance will be back to full speed.

Figure 1-3 Thermal Throttling Mechanism



Note:

1. The temperature for TMT is based on T_{case} . (T_{case} : temperature value of on SSD thermal sensor)
2. TMT levels may be varying by different workloads.

1.5. Advanced Device Security Features

1.5.1. Secure Erase

Secure Erase is a standard ATA command and will write all "0xFF" to fully wipe all the data on hard drives and SSDs. When this command is issued, SSD controller will erase its storage blocks and return to its factory default settings.

1.5.2. Physical Presence SID (PSID)

Physical Presence SID (PSID) is defined by TCG as a 32-character string and the purpose is to revert SSD back to its manufacturing setting. PSID code is printed on an SSD label.

1.5.3. Crypto Erase

Crypto Erase (TCG) is a feature that erases all data of an OPAL-activated SSD drive by resetting the cryptographic key of the disk. Since the key is modified, the previously encrypted data will become useless, achieving the purpose of data security.

1.5.4. TCG OPAL

Trusted Computing Group (TCG) provides a scalable infrastructure for managing encryption of user data in a Storage Device, as well as extensibility to enable feature. One set of capabilities defined in the Core Spec includes

mechanisms for managing access control to user data stored on the Storage Device, including controlling media encryption, Key Management, and Read/Write Lock State.

1.5.5. IEEE1667

IEEE 1667 is supported but needs to be activated by vendor tool when needed, this is to prevent unintended eDrive implementation and the following necessity of Reverting by PSID before being able to re-install Operation System. Table 1-2 illustrates the types of Sanitize Operation supported

Table 1-2 Drive Security Type

Drive Security Type	AES-256 Encryption	Sanitize Operation			TCG Commands		IEEE 1667
		Overwrite	Block Erase	Crypto Erase	PSID Revert Process	Instant Security Erase	Windows eDrive
SED (TCG Opal)	Yes	No	Yes	Yes	Yes ¹	Yes ²	Yes ³
Non-SED	No	No	Yes	No	No	No	No

NOTES:

1. Crypto Erase is a feature that erases all data of AES encrypted data structure by resetting the cryptographic key of the disk. The previously encrypted data will become irretrievable.
2. Instant Security Erase is a feature that erases all data of SED drive with Opal-activated encrypted data structure by reverting SSD with PSID. Since the key is reset, the previously encrypted data cannot be accessed anymore.
3. IEEE 1667 is supported but needs to be activated by vendor tool when needed, this is to prevent unintended eDrive implementation and the following necessity of Reverting by PSID before being able to re-install Operation System.

1.6. SSD Lifetime Management

1.6.1. Terabytes Written (TBW)

TBW (Terabytes Written) is a measurement of SSDs' expected lifespan, which represents the amount of data written to the device. To calculate the TBW of an SSD, the following equation is applied:

$$TBW (TB) = [DWPD * SSD Capacity(GB) * Warranty Days] / 1000$$

DWPD: Drive Writes Per Day

SSD Capacity: The SSD capacity is the specific capacity in total of an SSD.

Warranty Days: Years*365days

TBW in this document is based on 4K random write.

1.6.2. Media Wear Indicator

Actual life indicator reported by SMART/Health Information Log Page (02h) Life Remaining by percentage.

1.6.3. Read Only Mode (End of Life)

When drive is aged by cumulated program/erase cycles, media worn-out may cause increasing numbers of later bad block. When the number of usable good blocks falls outside a defined usable range, the drive will notify Host through

AER event and Critical Warning to enter Read Only Mode to prevent further data corruption. User should start to replace the drive with another one immediately.

1.7. Enterprise Feature

1.7.1. Namespace

Namespace is a collection of (LBA) accessible to host software. Host Divides an NVMe SSD into logically separate and individually addressable storage spaces. A namespace ID (NSID) is a unique ID and an identifier which can help the host to distinguish different namespace. So when we are going to read or write, the NSID is needed to be specified in the command to indicate which logic block we are going to operate. Each created NS, for a Host OS, is a separate disk, user can do partition and other operations in each NS.

1.7.2. Reservation

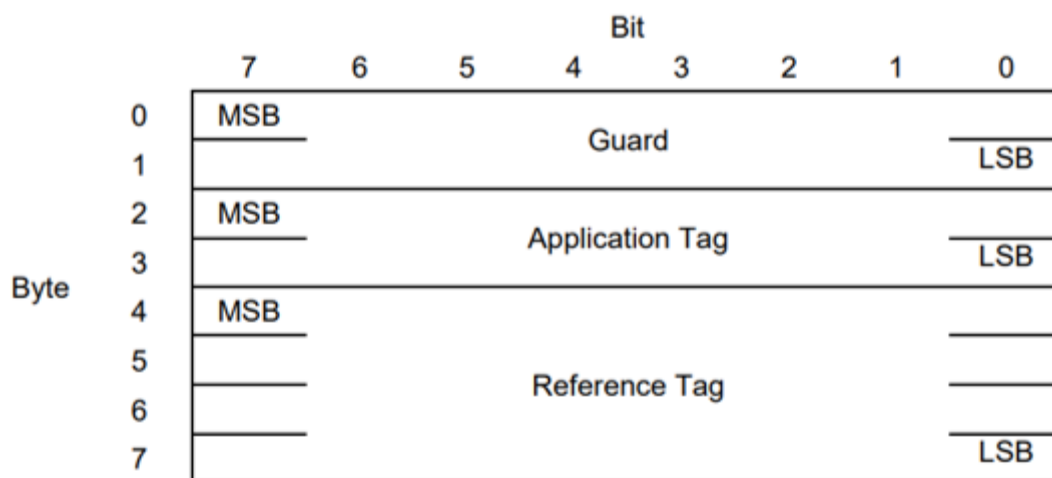
NVMe reservation commands manage the access authorization of multiple hosts to a single namespace. If a host submits a command to a namespace in the presence of a reservation and lacks sufficient rights, then the command will be aborted by the controller with a status of "Reservation Conflict".

There are three level of hosts, reservation Holder, registrant and non-registrant. Basically, there is only one reservation holder for a shared namespace. And the second level "registrants", are who have the reservation key, including the reservation holder. The non-registrant is the host who doesn't have the reservation key.

1.7.3. Metadata Protection

Metadata protection is an End to End Data Protection mechanism to ensure data integrity during data transfer which is realized by transmitting protection info with the LBA data. There are two ways to implement the metadata, one is DIF (Data integrity Field), and it stored together with logic block data. Another way is DIX (Data integrity Extension), it is to put the metadata elsewhere. Figure 1-4 is the diagram of Metadata format.

Figure 1-4 The Diagram of Metadata Format



The "Guard" is a 16-bit CRC, which is calculated from the LBA; "Application Tag" and "Reference Tag" ensure that the data does not appear mismatch problem, such as LBA X uses LBA Y data. CRC check can detect whether the data is wrong, the latter can ensure that the data does not appear mismatch problem, such as LBA X uses LBA Y data, which situation is often caused by SSD firmware Bug.

2. PRODUCT SPECIFICATIONS

2.1. Electrical/Physical Interface

- PCIe Interface
- Compliant with NVMe 1.4
- PCIe Express Base Ver 4.0
- PCIe Gen 4 x 4 lanes & backward compatible to PCIe Gen 3, Gen 2 and Gen 1 Device Capacity

Table 2-1 User Capacity and Addressable Sectors

EPM9970

DWPD = 1	User Addressable Sectors	Bytes per Sector
1920GB	3,750,748,848	512 Byte
3840GB	7,501,476,528	
7680GB	15,002,931,888	
15360GB	30,005,842,608	
30720GB	60,011,664,048	

EPW9970

DWPD = 3	User Addressable Sectors	Bytes per Sector
800GB	1,562,824,368	512 Byte
1600GB	3,125,627,568	
3200GB	6,251,233,968	
6400GB	12,502,446,768	
12800GB	25,004,872,368	
25600GB	50,009,723,568	

NOTES:

1. 1 Gigabyte (GB) is equal to 1,000,000,000 bytes; 1 sector is equal to 512 bytes.
2. The total actual usable capacity of the SSD may be less than the total physical capacity because internal NAND management, SSD format, SSD partition, operating system and so on.
3. The count of User Addressable Sectors is calculated by the formula of IDEMA.

2.2. Performance

2.2.1. Sequential Read/Write Performance and 4K Sustained Random Read/ Write Performance

Table 2-2 15mm High Performance Sequential Read/Write Performance and 4K Sustained Random Read/ Write Performance

Capacity	Model	Maximum Performance ¹			
		Sequential 128KB (QD=32, Workers=1)		4K Sustained Random (QD=64, , Workers=8)	
		Read (MB/s)	Write (MB/s)	Read (IOPS)	Write (IOPS)
800GB	EPW9970	6,650	1,710	950,000	104,500
1600GB	EPW9970	6,650	3,325	1,520,000	266,000
1920GB	EPM9970	6,650	3,325	1,520,000	90,250

Capacity	Model	Maximum Performance ¹			
		Sequential 128KB (QD=32, Workers=1)		4K Sustained Random (QD=64, , Workers=8)	
		Read (MB/s)	Write (MB/s)	Read (IOPS)	Write (IOPS)
3200GB	EPW9970	6,650	6,460	1,520,000	408,500
3840GB	EPM9970	6,650	6,460	1,520,000	161,500
6400GB	EPW9970	6,650	6,460	1,520,000	427,500
7680GB	EPM9970	6,650	6,460	1,520,000	171,000
12800GB	EPW9970	6,650	6,460	1,520,000	456,000
15360GB	EPM9970	6,650	6,460	1,520,000	171,000
25600 GB	EPW9970	TBD	TBD	TBD	TBD
30720 GB	EPM9970	TBD	TBD	TBD	TBD

Table 2-3 15mm Mainstream Sequential Read/Write Performance and 4K Sustained Random Read/ Write Performance

Capacity	Model	Maximum Performance ¹			
		Sequential 128KB (QD=32, Workers=1)		4K Sustained Random (QD=64, , Workers=8)	
		Read (MB/s)	Write (MB/s)	Read (IOPS)	Write (IOPS)
800GB	EPW9970	6,650	1,710	950,000	104,500
1600 GB	EPW9970	6,650	3,135	950,000	190,000
1920 GB	EPM9970	6,650	3,135	950,000	57,000
3200 GB	EPW9970	6,650	3,135	950,000	209,000
3840 GB	EPM9970	6,650	3,135	950,000	85,500
6400 GB	EPW9970	6,650	3,135	950,000	209,000
7680 GB	EPM9970	6,650	3,135	950,000	85500
12800 GB	EPW9970	4,275	2,375	712,500	142,500
15360 GB	EPM9970	4,275	2,375	712,500	57,000
25600 GB	EPW9970	TBD	TBD	TBD	TBD
30720 GB	EPM9970	TBD	TBD	TBD	TBD

Table 2-4 7mm Mainstream Sequential Read/Write Performance and 4K Sustained Random Read/ Write Performance

Capacity	Model	Maximum Performance ¹			
		Sequential 128KB (QD=32, Workers=1)		4K Sustained Random (QD=64, Workers=8)	
		Read (MB/s)	Write (MB/s)	Read (IOPS)	Write (IOPS)
800 GB	EPW9970	6,650	1,710	950,000	114,000
1600 GB	EPW9970	5,225	2,375	912,000	142,500
1920 GB	EPM9970	5,225	2,375	912,000	47,500
3200 GB	EPW9970	5,225	2,375	912,000	152,000
3840 GB	EPM9970	5,225	2,375	912,000	57,000
6400 GB	EPW9970	5,225	2,375	912,000	152,000
7680 GB	EPM9970	5,225	2,375	912,000	57,000

NOTES:

1. Performance was estimated based on SK hynix V6 eTLC NAND flash.
2. Performance may differ according to flash configuration and platform.
3. The tables are for reference only. Any criteria for accepting goods shall be further discussed based on different flash configurations.

2.3. Latency

2.3.1. Latency

Table 2-5 15mm High Performance 4KB Sustained Random Read/Write Latency

Capacity	Model	4K Sustained Random (QD=1, Workers=1)		4K Sustained Random (QD=32, Workers=1)		4K Sustained Random (QD=64, Workers=8)	
		Read	Write	Read	Write	Read	Write
		μs	μs	μs	μs	μs	μs
800 GB	EPW9970	91	16	101	281	561	4351
1600 GB	EPW9970	91	16	101	131	321	2001
1920 GB	EPM9970	91	16	101	351	321	5601
3200 GB	EPW9970	91	16	101	81	321	1251
3840 GB	EPM9970	91	16	101	201	321	3151
6400 GB	EPW9970	91	16	101	81	321	1251
7680 GB	EPM9970	91	16	101	201	321	3151
12800 GB	EPW9970	91	16	101	81	321	1101
15360 GB	EPM9970	91	16	101	181	321	2801
25600 GB	EPW9970	TBD	TBD	TBD	TBD	TBD	TBD
30720 GB	EPM9970	TBD	TBD	TBD	TBD	TBD	TBD

Table 2-6 15mm Mainstream 4KB Sustained Random Read/Write Latency

Capacity	Model	4K Sustained Random (QD=1, Workers=1)		4K Sustained Random (QD=32, Workers=1)		4K Sustained Random (QD=64, Workers=8)	
		Read	Write	Read	Write	Read	Write
		μs	μs	μs	μs	μs	μs
800GB	EPW9970	91	16	101	281	561	4351
1600 GB	EPW9970	111	16	121	171	491	2701
1920 GB	EPM9970	111	16	121	471	491	7601
3200 GB	EPW9970	101	16	111	151	481	2301
3840 GB	EPM9970	101	16	111	351	481	5601
6400 GB	EPW9970	101	16	111	161	461	2601
7680 GB	EPM9970	101	16	111	391	461	6101
12800 GB	EPW9970	101	16	111	231	731	3501
15360 GB	EPM9970	101	16	111	431	731	6701
25600 GB	EPW9970	TBD	TBD	TBD	TBD	TBD	TBD
30720 GB	EPM9970	TBD	TBD	TBD	TBD	TBD	TBD

Table 2-7 7mm Mainstream 4KB Sustained Random Read/Write Latency

Capacity	Model	4K Sustained Random (QD=1, Workers=1)		4K Sustained Random (QD=32, Workers=1)		4K Sustained Random (QD=64, Workers=8)	
		Read	Write	Read	Write	Read	Write
		μs	μs	μs	μs	μs	μs
800 GB	EPW9970	91	16	101	281	561	4351
1600 GB	EPW9970	101	16	111	241	581	3801
1920 GB	EPM9970	106	26	111	681	581	11001
3200 GB	EPW9970	101	16	111	201	581	3101
3840 GB	EPM9970	101	21	111	421	581	7501
6400 GB	EPW9970	101	16	111	201	581	3201
7680 GB	EPM9970	101	21	111	541	581	8301

NOTES:

1. Performance was estimated based on SK hynix V6 eTLC NAND flash.
2. Performance may differ according to flash configuration and platform.

- The tables are for reference only. Any criteria for accepting goods shall be further discussed based on different flash configurations.

2.4. IOPS Consistency

2.4.1. IOPS Consistency

Table 2-8 X 15mm High Performance 4KB Sustained Random Read/Write IOPS Consistency

Capacity	Model	4K Sustained Random (QD=1, Workers=1)		4K Sustained Random (QD=32, Workers=1)		4K Sustained Random (QD=64, Workers=8)	
		Read	Write	Read	Write	Read	Write
		%	%	%	%	%	%
800 GB	EPW9970	96	95	95	95	95	95
1600 GB	EPW9970	96	95	95	95	95	95
1920 GB	EPM9970	96	95	95	95	95	95
3200 GB	EPW9970	96	95	95	95	95	95
3840 GB	EPM9970	96	95	95	95	95	95
6400 GB	EPW9970	96	95	95	95	95	95
7680 GB	EPM9970	96	95	95	95	95	95
12800 GB	EPW9970	96	95	95	95	95	95
15360 GB	EPM9970	96	95	95	95	95	95
25600 GB	EPW9970	TBD	TBD	TBD	TBD	TBD	TBD
30720 GB	EPM9970	TBD	TBD	TBD	TBD	TBD	TBD

Table 2-9 15mm Mainstream 4KB Sustained Random Read/Write IOPS Consistency

Capacity	Model	4K Sustained Random (QD=1, Workers=1)		4K Sustained Random (QD=32, Workers=1)		4K Sustained Random (QD=64, Workers=8)	
		Read	Write	Read	Write	Read	Write
		%	%	%	%	%	%
800 GB	EPW9970	95	95	95	95	95	95
1600 GB	EPW9970	95	95	95	95	95	95
1920 GB	EPM9970	95	95	95	95	95	95
3200 GB	EPW9970	95	95	95	95	95	95
3840 GB	EPM9970	95	95	95	95	95	95
6400 GB	EPW9970	95	95	95	95	95	95

Capacity	Model	4K Sustained Random (QD=1, Workers=1)		4K Sustained Random (QD=32, Workers=1)		4K Sustained Random (QD=64, Workers=8)	
		Read	Write	Read	Write	Read	Write
		%	%	%	%	%	%
7680 GB	EPM9970	95	95	95	95	95	95
12800 GB	EPW9970	95	95	95	95	95	95
15360 GB	EPM9970	95	95	95	95	95	95
25600 GB	EPW9970	TBD	TBD	TBD	TBD	TBD	TBD
30720 GB	EPM9970	TBD	TBD	TBD	TBD	TBD	TBD

Table 2-10 7mm Mainstream 4KB Sustained Random Read/Write IOPS Consistency

Capacity	Model	4K Sustained Random (QD=1, Workers=1)		4K Sustained Random (QD=32, Workers=1)		4K Sustained Random (QD=64, Workers=8)	
		Read	Write	Read	Write	Read	Write
		%	%	%	%	%	%
800 GB	EPW9970	95	95	95	95	95	95
1600 GB	EPW9970	95	95	95	95	95	95
1920 GB	EPM9970	95	95	95	95	95	95
3200 GB	EPW9970	95	95	95	95	95	95
3840 GB	EPM9970	95	95	95	95	95	95
6400 GB	EPW9970	95	95	95	95	95	95
7680 GB	EPM9970	95	95	95	95	95	95

NOTES:

1. Consistency Definition: $100 - [(mean_IOPS - min_IOPS) / mean_IOPS]$
2. Performance was estimated based on SK hynix V6 eTLC NAND flash.
3. Performance may differ according to flash configuration and platform.
4. The tables are for reference only. Any criteria for accepting goods shall be further discussed based on different flash configurations.

2.5. Quality of Service (QoS=99%)

Table 2-11 15mm High Performance: 4KB Sustained Random Read/Write Quality of Service (QoS=99%) 1ms =1000us

Capacity	Model	4KB Sustained Random Read/Write Quality of Service (QoS=99%) ¹					
		(QD=1, Workers=1)		(QD=32, Workers=1)		(QD=64, Workers=8)	
		Read (4KB)	Write (4KB)	Read (4KB)	Write (4KB)	Read (4KB)	Write (4KB)
		μs	μs	μs	μs	μs	μs
800 GB	EPW9970	101	13	201	281	2401	4501
1600 GB	EPW9970	101	13	161	131	1001	2001
1920 GB	EPM9970	101	13	161	351	1001	5701
3200 GB	EPW9970	101	13	141	101	601	2001
3840 GB	EPM9970	101	13	141	201	601	3201
6400 GB	EPW9970	101	13	131	101	601	1801
7680 GB	EPM9970	101	13	131	201	601	3201
12800 GB	EPW9970	101	13	121	81	601	1601
15360 GB	EPM9970	101	13	121	181	601	3001
25600 GB	EPW9970	TBD	TBD	TBD	TBD	TBD	TBD
30720 GB	EPM9970	TBD	TBD	TBD	TBD	TBD	TBD

Table 2-12 15mm Mainstream: 4KB Sustained Random Read/Write Quality of Service (QoS=99%) 1ms =1000us

Capacity	Model	4KB Sustained Random Read/Write Quality of Service (QoS=99%) ¹					
		(QD=1, Workers=1)		(QD=32, Workers=1)		(QD=64, Workers=8)	
		Read (4KB)	Write (4KB)	Read (4KB)	Write (4KB)	Read (4KB)	Write (4KB)
		μs	μs	μs	μs	μs	μs
800 GB	EPW9970	101	13	201	281	2401	4501
1600 GB	EPW9970	121	16	201	171	801	2701
1920 GB	EPM9970	121	16	201	481	781	7601
3200 GB	EPW9970	121	16	181	141	611	2301
3840 GB	EPM9970	121	16	181	351	611	5601
6400 GB	EPW9970	121	16	161	161	561	2551
7680 GB	EPM9970	121	16	161	391	561	6101
12800 GB	EPW9970	121	16	231	231	781	3601
15360 GB	EPM9970	121	16	141	431	701	6801
25600 GB	EPW9970	TBD	TBD	TBD	TBD	TBD	TBD

Capacity	Model	4KB Sustained Random Read/Write Quality of Service (QoS=99%) ¹					
		(QD=1, Workers=1)		(QD=32, Workers=1)		(QD=64, Workers=8)	
		Read (4KB)	Write (4KB)	Read (4KB)	Write (4KB)	Read (4KB)	Write (4KB)
		μs	μs	μs	μs	μs	μs
30720 GB	EPM9970	TBD	TBD	TBD	TBD	TBD	TBD

Table 2-13 7mm Mainstream: 4KB Sustained Random Read/Write Quality of Service (QoS=99%) 1ms =1000us

Capacity	Model	4KB Sustained Random Read/Write Quality of Service (QoS=99%) ¹					
		(QD=1, Workers=1)		(QD=32, Workers=1)		(QD=64, Workers=8)	
		Read (4KB)	Write (4KB)	Read (4KB)	Write (4KB)	Read (4KB)	Write (4KB)
		μs	μs	μs	μs	μs	μs
800 GB	EPW9970	101	13	201	281	2401	4501
1600 GB	EPW9970	116	13	201	241	801	3801
1920 GB	EPM9970	116	21	201	681	801	11001
3200 GB	EPW9970	116	13	181	201	701	3101
3840 GB	EPM9970	116	21	181	471	701	7501
6400 GB	EPW9970	116	13	161	201	661	3201
7680 GB	EPM9970	116	21	161	551	661	8401

2.6. Weight

Table 2-14 15mm Weight

Capacity	Flash Configuration	Flash Type	Weight (g)
800GB	256GB x 4	16CE, 512Gb, QDP	197
1600GB	256GB x 8	32CE, 512Gb, QDP	198
1920GB	256GB x 8	32CE, 512Gb, QDP	198
3200GB	256GB x 16	64CE, 512Gb QDP	200
3840GB	256GB x 16	64CE, 512Gb QDP	200
6400GB	512GB x 16	128CE, 512Gb ODP	203
7680GB	512GB x 16	128CE, 512Gb ODP	203
12800GB	512GB x 32	128CE, 512Gb ODP	TBD
15360GB	512GB x 32	128CE, 512Gb ODP	TBD
25600GB	1024GB x 32	128CE, 512Gb HDP	TBD
30720GB	1024GB x 32	128CE, 512Gb HDP	TBD

Table 2-15 7mm Weight

Capacity	Flash Configuration	Flash Type	Weight (g)
800GB	256GB x 4	16CE, 512Gb, QDP	91
1600GB	256GB x 8	32CE, 512Gb, QDP	92
1920GB	256GB x 8	32CE, 512Gb, QDP	92
3200GB	256GB x 16	64CE, 512Gb QDP	98
3840GB	256GB x 16	64CE, 512Gb QDP	98
6400GB	512GB x 16	128CE, 512Gb ODP	104
7680GB	512GB x 16	128CE, 512Gb ODP	104

3. ENVIRONMENTAL SPECIFICATIONS

3.1. Environmental Conditions

3.1.1. Temperature and Humidity

Table 3-1 Temperature and Humidity Specification

Temperature	Operating	0°C to 70°C
	Non-operating	-40°C to 85°C
Relative Humidity	Operating	5% to 95%
	Non-operating	5% to 95%

3.1.2. Shock

Table 3-2 Shock

	Type	Acceleration	Pulse Duration
Shock	Operating	500G	2ms
		1000G	1000ms
	Non-operating	500G	2ms
		1000G	1000ms

3.1.3. Vibration

Table 3-3 Vibration

	Operating Type	Frequency	Amplitude
Vibration	Operating	200 to 2000 Hz	2.17 Grms
		10 - 2000 Hz	16.3 Grms
	Non-operating	2 - 5 - 500 Hz	3 Grms

3.1.4. Altitude

Table 3-4 Altitude

	Operating Type	Value
Altitude	Operating	0 to 18,000 feet
	Non-operating	0 to 40,000 feet

3.2. TBW (Terabytes Written) and DDPD (Drive Write Per Day)

Table 3-5 TBW & DWPD

Capacity	Model Name	Flash Structure	Flash Type	TBW	DWPD
800GB	EPW9970	256GB x 4	SK hynix V6 3D eTLC	4380	3
1600GB	EPW9970	256GB x 8	SK hynix V6 3D eTLC	8760	3
1920GB	EPM9970	256GB x 8	SK hynix V6 3D eTLC	3504	1
3200GB	EPW9970	256GB x 16	SK hynix V6 3D eTLC	17520	3
3840GB	EPM9970	256GB x 16	SK hynix V6 3D eTLC	7008	1
6400GB	EPW9970	512GB x 16	SK hynix V6 3D eTLC	35040	3
7680GB	EPM9970	512GB x 16	SK hynix V6 3D eTLC	14016	1
12800GB	EPW9970	512GB x 32	SK hynix V6 3D eTLC	70080	3
15360GB	EPM9970	512GB x 32	SK hynix V6 3D eTLC	28032	1

3.3. Power On/Off Cycles

The definition of power on/off cycles is that the power is withdrawn from the SSD device, and then restored. The test is to simulate the behavior that SSD still can be restored and active normally when host platforms go into suspend and shutdown.

During the Power On/Off cycles test, the SSD can be protective if the SSD encounters 24 times of power on/off per day within warranty period.

3.4. UBER

Table 3-6 UBER

Capacity	Flash Type	UBER
800GB	3D NAND	< 1 sector per 10 ¹⁸ bits read
1600GB		
1920GB		
3200GB		
3840GB		
6400GB		
7680GB		
15360GB		
12800GB		

NOTE:

1. UBER (Uncorrectable Bit Error Rates) means the uncorrectable error per bits read.

3.5. Mean Time Between Failures

Mean Time Between Failures(MTBF) is demonstrated through a 2,000-hour Reliability Demonstration Test.

Table 3-7 MTBF

Description	Value
Mean Time Between Failures	2.5 million hours

4. ELECTRICAL SPECIFICATIONS

4.1. Supply Voltage

Table 4-1 Supply Voltage

	800 GB	1600 GB	3200 GB	6400 GB	1920 GB	3840 GB	7680 GB	12800 GB	15360 GB	25600 GB	30720 GB
12v	+/- 10%										
12v noise level	240mVp-p, 0-20MHz										
12v min off time	500ms										
3.3v aux	+/- 15%										

NOTE:

1. Minimum time between power removed from SSD ($V_{cc} < 100$ mV) and power re-applied to the drive.

4.2. Power Consumption

Table 4-2 Power Consumption

Form Factor	Capacity	Random Read(Typ.,W)	Random Write(Typ.,W)	Sequential Read(Typ.,W)	Sequential Write(Typ., W)	Idle (Typ., W)
15mm High Performance	800 GB	8.4	8.3	8.8	7.9	4.7
	1600 GB	12.2	11.9	9.9	12.7	5.3
	1920 GB	11.8	11.4	9.6	12.2	5.2
	3200 GB	13.2	15.6	10.5	17.4	5.6
	3840 GB	12.7	14.8	10.1	17.1	5.6
	6400 GB	15.2	17	11.4	19	5.6
	7680 GB	15	16.6	11.1	18.2	5.5
	12800 GB	15.7	19.2	12	19.8	7.1
	15360 GB	15.4	18.7	11.7	19.1	7
	25600 GB	TBD	TBD	TBD	TBD	TBD
30720 GB	TBD	TBD	TBD	TBD	TBD	
15mm Mainstream	1600 GB	9.6	9.7	9.6	10.6	5
	1920 GB	9.2	9.4	9.1	10.4	4.8
	3200 GB	10.3	10.1	9.8	10.5	5.3
	3840 GB	9.7	9.7	9.4	10.4	4.9
	6400 GB	11.5	11.4	11.4	11.5	5.6
	7680 GB	11.2	10.6	11	11.4	5.3
	12800 GB	11.7	11.6	10.7	11.6	6.8
	15360 GB	11.4	11.2	10.3	11.2	6.6
	25600 GB	TBD	TBD	TBD	TBD	TBD
30720 GB	TBD	TBD	TBD	TBD	TBD	
7mm Mainstream	800 GB	8.2	8	8.7	7.9	4.8
	1600 GB	8.9	8.8	8.9	9.7	5.1
	1920 GB	8.5	8.9	8.4	9.3	4.8
	3200 GB	9.5	9.4	9.2	9.8	5

Form Factor	Capacity	Random Read(Typ.,W)	Random Write(Typ.,W)	Sequential Read(Typ.,W)	Sequential Write(Typ., W)	Idle (Typ., W)
	3840 GB	9.2	9.5	9	9.5	5.1
	6400 GB	10.2	10.5	10.1	10.7	5.1
	7680 GB	10	10	10	10.5	5.1

NOTES:

1. Power consumption is measured on full speed mode.

4.3. Inrush Current

Table 4-3 Inrush Current

Inrush current	800 GB	1600GB/1920GB	3200GB/3840GB	6400GB/7680GB	12800GB/15360GB	25600GB/30720GB
12v	1.5A					TBD

5. INTERFACE

5.1. PCIe U.3 and U.2 Pin Assignment and Descriptions

Figure 5-1 X1 U.3 PCIe SSD Pin Assignment

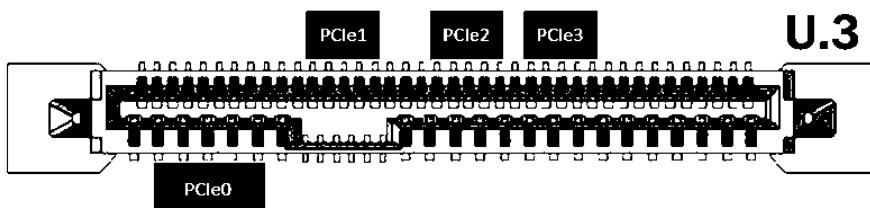


Figure 5-2 X1 U.2 PCIe SSD Pin Assignment

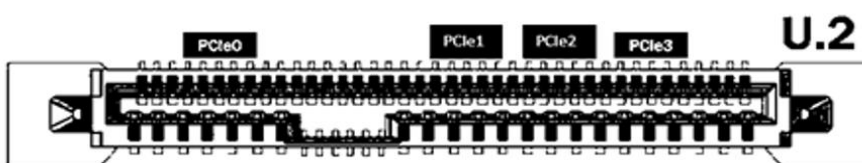


Table 5-1 Pin Assignment and Descriptions

Pin No.	Name	Type	Description
P1	WAKE#	Input	Reserved
P2	Reserved	Reserved	Reserved
P3	PWRDIS	Output	Power disable
P4	IfDet#	Input	Interface Type Detect
P5	Ground	Ground	Ground
P6	Ground	Ground	Ground
P7	+5V	Power	Reserved
P8	+5V	Power	Reserved
P9	+5V	Power	Reserved
P10	PRSNT#	Input	Presence detect
P11	Activity#	Input	Activity indicator
P12	Ground	Ground	Ground
P13	+12V Precharge	Power	+12V Precharge power
P14	+12V	Power	+12V power
P15	+12V	Power	+12V power
SG1	Ground	Ground	Ground
SG2	Ground	Ground	Ground
S1	Ground	Ground	Ground
S2	U.3 TX p0	Diff-Pair	Transmitter differential pair, U.3 Lane 0
S3	U.3 TX n0	Diff-Pair	Transmitter differential pair, U.3 Lane 0
S4	Ground	Ground	Ground
S5	U.3 RX n0	Diff-Pair	Receiver differential pair, U.3 Lane 0
S6	U.3 RX p0	Diff-Pair	Receiver differential pair, U.3 Lane 0

Pin No.	Name	Type	Description
S7	Ground	Ground	Ground
S8	Ground	Ground	Ground
S9	U.3 TX p1	Diff-Pair	Transmitter differential pair, U.3 Lane 1
S10	U.3 TX n1	Diff-Pair	Transmitter differential pair, U.3 Lane 1
S11	Ground	Ground	Ground
S12	U.3 RX n1	Diff-Pair	Receiver differential pair, U.3 Lane 1
S13	U.3 RX p1	Diff-Pair	Receiver differential pair, U.3 Lane 1
S14	Ground	Ground	Ground
S15	HPT0	Output	Host port type
S16	Ground	Ground	Ground
S17	U.3 TX p2/ U.2 TX p1	Diff-Pair	Transmitter differential pair, U.3 Lane 2, or U.2 Lane 1
S18	U.3 TX n2/ U.2 TX n1	Diff-Pair	Transmitter differential pair, U.3 Lane 2, or U.2 Lane 1
S19	Ground	Ground	Ground
S20	U.3 RX n2/ U.2 RX n1	Diff-Pair	Receiver differential pair, U.3 Lane 2, or U.2 Lane 1
S21	U.3 RX p2/ U.2 RX p1	Diff-Pair	Receiver differential pair, U.3 Lane 2, or U.2 Lane 1
S22	Ground	Ground	Ground
S23	U.3 TX p3/ U.2 TX p2	Diff-Pair	Transmitter differential pair, U.3 Lane 3, or U.2 Lane 2
S24	U.3 TX n3/ U.2 TX n2	Diff-Pair	Transmitter differential pair, U.3 Lane 3, or U.2 Lane 2
S25	Ground	Ground	Ground
S26	U.3 RX n3/ U.2 RX n2	Diff-Pair	Receiver differential pair, U.3 Lane 3, or U.2 Lane 2
S27	U.3 RX p3/ U.2 RX p2	Diff-Pair	Receiver differential pair, U.3 Lane 3, or U.2 Lane 2
S28	Ground	Ground	Ground
E1	REFCLKB+	Diff-Pair	Reference clock (differential pair) for second X2 port
E2	REFCLKB-	Diff-Pair	Reference clock (differential pair) for second X2 port
E3	+3.3 Vaux	Power	3.3 V auxiliary power
E4	CLKREQ#/PERSTB#	Bi-dir	Clock request/Fundamental reset for second x2 port
E5	PERST#	Output	Fundamental reset
E6	IFDet2#	Input	Interface Type Detect
E7	REFCLK+	Diff-Pair	Reference clock
E8	REFCLK-	Diff-Pair	Reference clock
E9	Ground	Ground	Ground
E10	U.2 TX p0	Diff-Pair	Transmitter differential pair, U.2 Lane 0
E11	U.2 TX n0	Diff-Pair	Transmitter differential pair, U.2 Lane 0
E12	Ground	Diff-Pair	Ground
E13	U.2 RX n0	Diff-Pair	Receiver differential pair, U.2 Lane 0
E14	U.2 RX p0	Diff-Pair	Receiver differential pair, U.2 Lane 0
E15	Ground	Ground	Ground
E16	HPT1	Output	Host port type
E17	U.2 TX p3	Diff-Pair	Transmitter differential pair, U.2 Lane 3
E18	U.2 TX n3	Diff-Pair	Transmitter differential pair, U.2 Lane 3
E19	Ground	Ground	Ground
E20	U.2 RX n3	Diff-Pair	Receiver differential pair, U.2 Lane 3

Pin No.	Name	Type	Description
E21	U.2 RX p3	Diff-Pair	Receiver differential pair, U.2 Lane 3
E22	Ground	Ground	Ground
E23	SMCLK	Bi-Dir	SMBus (System Management Bus) clock
E24	SMDAT	Bi-Dir	SMBus (System Management Bus) data
E25	DualPortEn#	Output	Dual-port Enable

6. SUPPORTED COMMANDS

6.1. NVMe Command List

Table 6-1 Admin Command List

Identifier	O/M	Supported	Command Description
00h	M	Y	Delete I/O Submission Queue
01h	M	Y	Create I/O Submission Queue
02h	M	Y	Get Log Page
04h	M	Y	Delete I/O Completion Queue
05h	M	Y	Create I/O Completion Queue
06h	M	Y	Identify
08h	M	Y	Abort
09h	M	Y	Set Feature
0Ah	M	Y	Get Feature
0Ch	M	Y	Asynchronous Event Request
0Dh	O	Y	Namespace Management
10h	O	Y	Firmware Commit
11h	O	Y	Firmware Image Download
14h	O	Y	Device Self-test
15h	O	Y	Namespace Attachment
18h	O	N	Keep Alive
19h	O	-	Directive Send
1Ah	O	-	Directive Receive
1Ch	O	-	Virtualization Management
1Dh	O	Y	NVMe-MI Send
1Eh	O	Y	NVMe-MI Receive
7Ch	O	-	Doorbell Buffer Config
80h	O	Y	Format NVM
81h	O	Y	Security Send
82h	O	Y	Security Receive
84h	O	Y	Sanitize
86h	O	-	Get LBA Status

Table 6-2 I/O Commands

Identifier	O/M	Supported	Command Description
00h	M	Y	Flush
01h	M	Y	Write
02h	M	Y	Read
04h	O	Y	Write Uncorrectable
05h	O	Y	Compare
08h	O	Y	Write Zeroes
09h	O	Y	Dataset Management (Trim only)
0Ch	O	Y	Verify

Identifier	O/M	Supported	Command Description
0Dh	O	Y	Reservation Register
0Eh	O	Y	Reservation Report
11h	O	Y	Reservation Acquire
15h	O	Y	Reservation Release

Table 6-3 Set Feature Commands

Identifier	O/M	Supported	Command Description
00h	-	-	Reserved
01h	M	Y	Arbitration
02h	M	Y	Power Management
03h	O	-	LBA Range Type
04h	M	Y	Temperature Threshold
05h	M	Y	Error Recovery
06h	O	Y	Volatile Write Cache
07h	M	Y	Number Of Queues
08h	M	Y	Interrupt Coalescing
09h	M	Y	Interrupt Vector Configuration
0Ah	M	Y	Write Atomicity Normal
0Bh	M	Y	Asynchronous Event Configuration
0Ch	O	-	Autonomous Power State Transition
0Dh	O	-	Host Memory Buffer
0Eh	O	Y	Timestamp
0Fh	O	Y	Keep Alive Timer
10h	O	-	Host Controlled Thermal Management
11h	O	-	Non-Operational Power State Config
12h	O	-	Read Recovery Level Config
13h	O	-	Predictable Latency Mode Config
14h	O	-	Predictable Latency Mode Window
15h	O	-	LBA Status Information Attributes
16h	O	-	Host Behavior Support
17h	O	Y	Sanitize Config
18h	O	-	Endurance Group Event Configuration
19h - 77h	-	-	Reserved (NVMe Reserved)
78h - 7Dh	-	-	Reserved(NVMe MI Reserved)
7Eh	M	Y	Controller Metadata (NVMe MI)
7Fh	M	Y	Namespace Metadata (NVMe MI)
80h	O	-	Software Progress Marker
81h	O	Y	Host Identifier
82h	O	Y	Reservation Notification Mask
83h	O	Y	Reservation Persistence
84h	O	-	Namespace Write Protection Config
85h - BFh	-	-	Command Set Specific (Reserved)

Identifier	O/M	Supported	Command Description
C0h - FFh	O	-	Vendor Specific

Table 6-4 Get Log Page Commands

Identifier	O/M	Supported	Command Description
00h	-	-	Reserved
01h	M	Y	Error Information
02h	M	Y	SMART / Health Information
03h	M	Y	Firmware Slot Information
04h	O	Y	Changed Namespace List
05h	O	Y	Commands Supported and Effects
06h	O	Y	Device Self-test
07h	O	Y	Telemetry Host-Initiated
08h	O	Y	Telemetry Controller-Initiated
09h	O	-	Endurance Group Information
0Ah	O	-	Predictable Latency Per NVM Set
0Bh	O	-	Predictable Latency Event Aggregate
0Ch	O	-	Asymmetric Namespace Access
0Dh	O	Y	Persistent Event Log
0Eh	O	-	LBA Status Information
0Fh	O	-	Endurance Group Event Aggregate
10h - 7Fh	-	-	Reserved
80h	O	Y	Reservation Notification
81h	O	Y	Sanitize Status
82h - FFh	-	-	Reserved

Table 6-5 NVMe Management Interface Commands

Identifier	O/M	Supported	Command Description
00h	M	Y	Read NVMe-MI Data Structure
01h	M	Y	NVM Subsystem Health Status Poll
02h	M	Y	Controller Health Status Poll
03h	M	Y	Configuration Set
04h	M	Y	Configuration Get
05h	M	Y	VPD Read
06h	M	Y	VPD Write
07h	M	Y	Reset
08h	-	-	SES Receive
09h	-	-	SES Send
0Ah	O	-	Management Endpoint Buffer Read
0Bh	O	-	Management Endpoint Buffer Write
0Ch - BFh	O	-	Reserved
C0h - FFh	O	-	Vendor Specific

NOTES:

1. “Y” means “Support”.
2. “O” means “Option, default No support”.
3. “-” means “No support”.

Table 6-6 SMBus / I2C Elements Supported

SMBus/I2C Element	SMBus/I2C Address(8bit)	
	Hex Format	Binary format
FRU Information Device (for NVMe Storage Device)	A6h	1010_011xb
SMBus/I2C Management Endpoint	3Ah	0011_101xb
Basic Management Command	D4h	1101_010xb

6.2. Identify Device Data

The following table details the sector data returned by the IDENTIFY DEVICE command.

Table 6-7 Identify Controller Data Structure

Bytes	O/M	Description	Default Value
01:00	M	PCI Vendor ID (VID)	0x1987
03:02	M	PCI Subsystem Vendor ID (SSVID)	0x1987
23:04	M	Serial Number (SN)	TBD
63:24	M	Model Number (MN)	TBD
71:64	M	Firmware Revision (FR)	TBD
72	M	Recommended Arbitration Burst (RAB)	0x01
75:73	M	IEEE OUI Identifier (IEEE)	TBD*
76	O	Controller Multi-Path I/O and Namespace Sharing Capabilities (CMIC)	0x03
77	M	Maximum Data Transfer Size (MDTS)	0x09
79:78	M	Controller ID (CNTLID)	0x0001
83:80	M	Version (VER)	0x00010400
87:84	M	RTD3 Resume Latency (RTD3R)	0x001E8480 (2 Sec)
91:88	M	RTD3 Entry Latency (RTD3E)	0x00989680
95:92	M	Optional Asynchronous Events Supported (OAES)	0x00000300
99:96	M	Controller Attributes (CTRATT)	0x00000000
101:100	O	Read Recovery Levels Supported (RRLS):	0x0000
110:102	-	Reserved	0x00
111	M	Controller Type (CNTRLTYPE)	0x01
127:112	O	FRU Globally Unique Identifier (FGUID):	TBD
129:128	O	Command Retry Delay Time 1 (CRDT1):	0x0000
131:130	O	Command Retry Delay Time 2 (CRDT2):	0x0000
133:132	O	Command Retry Delay Time 3 (CRDT3):	0x0000
239:134		Reserved	
255:240	-	Refer to the NVMe Management Interface Specification for definition	0x00
257:256	M	Optional Admin Command Support (OACS)	0x005F
258	M	Abort Command Limit (ACL)	0x07
259	M	Asynchronous Event Request Limit (AERL)	0x0E

Bytes	O/M	Description	Default Value
260	M	Firmware Updates (FRMW)	0x1C
261	M	Log Page Attributes (LPA)	0x1E
262	M	Error Log Page Entries (ELPE)	0x3E
263	M	Number of Power States Support (NPSS)	3
264	M	Admin Vendor Specific Command Configuration (AVSCC)	0x01
265	O	Autonomous Power State Transition Attributes (APSTA)	0x00
267:266	M	Warning Composite Temperature Threshold (WCTEMP)	0x0157 (70C)
269:268	M	Critical Composite Temperature Threshold (CCTEMP)	0x0161 (80C)
271:270	O	Maximum Time for Firmware Activation (MTFA)	0x0032
275:272	O	Host Memory Buffer Preferred Size (HMPRE)	0x00000000
279:276	O	Host Memory Buffer Minimum Size (HMMIN)	0x00000000
295:280	O	Total NVM Capacity (TNVMCAP)	**
311:296	O	Unallocated NVM Capacity (UNVMCAP)	**
315:312	O	Replay Protected Memory Block Support (RPMBS)	0x00000000
317:316	O	Extended Device Self-test Time (EDSTT)	0x0002
318	O	Device Self-test Options (DSTO)	0x01
319	O	Firmware Update Granularity (FWUG)	0x01
321:320	O	Keep Alive Support (KAS)	0x0000
323:322	O	Host Controlled Thermal Management Attributes (HCTMA)	0x0001
325:324	O	Minimum Thermal Management Temperature (MNTMT)	0x0111
327:326	O	Maximum Thermal Management Temperature (MXTMT)	0x0157
331:328	O	Sanitize Capabilities (SANICAP)	0x60000003
335:332	O	Host Memory Buffer Minimum Descriptor Entry Size (HMMINDS):	0x00000000
337:336	O	Host Memory Maximum Descriptors Entries (HMMAXD):	0x0000
339:338	O	NVM Set Identifier Maximum (NSETIDMAX):	0x0000
341:340	O	Endurance Group Identifier Maximum (ENDGIDMAX):	0x0000
342	O	ANA Transition Time (ANATT):	0x00
343	O	Asymmetric Namespace Access Capabilities (ANACAP):	0x00
347:344	O	ANA Group Identifier Maximum (ANAGRPMAX):	0x00000000
351:348	O	Number of ANA Group Identifiers (NANAGRPID):	0x00000000
355:352	O	Persistent Event Log Size (PELS):	0x63
511:356		Reserved	0x0

Table 6-8 NVM Command Set Attributes

NVM Command Set Attributes			
512	M	Submission Queue Entry Size (SQES)	0x66
513	M	Completion Queue Entry Size (CQES)	0x44
515:514		Maximum Outstanding Commands (MAXCMD)	0x0400 1 port 0x0200 2 port
519:516	M	Number of Namespaces (NN)	0x00000080
521:520	M	Optional NVM Command Support (ONCS)	0x00FF
523:522	M	Fused Operation Support (FUSES)	0x0000
524	M	Format NVM Attributes (FNA)	0x04

NVM Command Set Attributes			
525	M	Volatile Write Cache (VWC)	0x07
527:526	M	Atomic Write Unit Normal (AWUN)	0x00FF
529:528	M	Atomic Write Unit Power Fail (AWUPF)	0x00FF
530	M	NVM Vendor Specific Command Configuration (NVSCC)	0x01
531	M	Namespace Write Protection Capabilities (NWPC):	0x00
533:532	O	Atomic Compare & Write Unit (ACWU)	0x0000
535:534	M	Reserved	0x0000
539:536	O	SGL Support (SGLS)	0x000F0001
543:540	O	Maximum Number of Allowed Namespaces (MNAN):	0x00000000
767:544	M	Reserved	0x00
1023:768	M	NVM Subsystem NVMe Qualified Name (SUBNQN):	TBD

Table 6-9 IO Command Set Attributes

IO Command Set Attributes			
2079:2048	M	Power State 0 Descriptor (PSD0)	
Bit[255:184]		Reserved	0x00
Bit[183:182]		Active Power Scale (APS)	0x0
Bit[181:179]		Reserved	0x0
Bit[178:176]		Active Power Workload (APW)	0x0
Bit[175:160]		Active Power (ACTP)	0x0
Bit[159:152]		Reserved	0x0
Bit[151:150]		Idle Power Scale (IPS)	0x0
Bit[149:144]		Reserved	0x0
Bit[143:128]		Idle Power (IDL P)	0x0
Bit[127:125]		Reserved	0x0
Bit[124:120]		Relative Write Latency (RWL)	0x0
Bit[119:117]		Reserved	0x0
Bit[116:112]		Relative Write Throughput (RWT)	0x0
Bit[111:109]		Reserved	0x0
Bit[108:104]		Relative Read Latency (RRL)	0x0
Bit[103:101]		Reserved	0x0
Bit[100:96]		Relative Read Throughput (RRT)	0x0
Bit[95:64]		Exit Latency (EXLAT)	0x0
Bit[63:32]		Entry Latency (ENLAT)	0x0
Bit[31:26]		Reserved	0x0
Bit[25]		Non-Operational State (NOPS)	0
Bit[24]		Max Power Scale (MPS)	0
Bit[23:16]		Reserved	0x0
Bit[15:0]		Maximum Power (MP)	0x37A
2111:2080	O	Power State 1 Descriptor (PSD1)	
Bit[255:184]		Reserved	0x00
Bit[183:182]		Active Power Scale (APS)	0x0
Bit[181:179]		Reserved	0x0
Bit[178:176]		Active Power Workload (APW)	0x0
Bit[175:160]		Active Power (ACTP)	0x0

IO Command Set Attributes			
Bit[159:152]		Reserved	0x0
Bit[151:150]		Idle Power Scale (IPS)	0x0
Bit[149:144]		Reserved	0x0
Bit[143:128]		Idle Power (IDL P)	0x0
Bit[127:125]		Reserved	0x0
Bit[124:120]		Relative Write Latency (RWL)	0x1
Bit[119:117]		Reserved	0x0
Bit[116:112]		Relative Write Throughput (RWT)	0x1
Bit[111:109]		Reserved	0x0
Bit[108:104]		Relative Read Latency (RRL)	0x1
Bit[103:101]		Reserved	0x0
Bit[100:96]		Relative Read Throughput (RRT)	0x1
Bit[95:64]		Exit Latency (EXLAT)	0x0
Bit[63:32]		Entry Latency (ENLAT)	0x0
Bit[31:26]		Reserved	0x0
Bit[25]		Non-Operational State (NOPS)	0
Bit[24]		Max Power Scale (MPS)	0
Bit[23:16]		Reserved	0x0
Bit[15:0]		Maximum Power (MP)	0xE6
2143:2112	0	Power State 2 Descriptor (PSD2)	
Bit[255:184]		Reserved	0x00
Bit[183:182]		Active Power Scale (APS)	0x0
Bit[181:179]		Reserved	0x0
Bit[178:176]		Active Power Workload (APW)	0x0
Bit[175:160]		Active Power (ACTP)	0x0
Bit[159:152]		Reserved	0x0
Bit[151:150]		Idle Power Scale (IPS)	0x0
Bit[149:144]		Reserved	0x0
Bit[143:128]		Idle Power (IDL P)	0x0
Bit[127:125]		Reserved	0x0
Bit[124:120]		Relative Write Latency (RWL)	0x2
Bit[119:117]		Reserved	0x0
Bit[116:112]		Relative Write Throughput (RWT)	0x2
Bit[111:109]		Reserved	0x0
Bit[108:104]		Relative Read Latency (RRL)	0x2
Bit[103:101]		Reserved	0x0
Bit[100:96]		Relative Read Throughput (RRT)	0x2
Bit[95:64]		Exit Latency (EXLAT)	0x0
Bit[63:32]		Entry Latency (ENLAT)	0x0
Bit[31:26]		Reserved	0x0
Bit[25]		Non-Operational State (NOPS)	0
Bit[24]		Max Power Scale (MPS)	0
Bit[23:16]		Reserved	0x0
Bit[15:0]		Maximum Power (MP)	0xB4
2175:2144	0	Power State 3 Descriptor (PSD3)	0x00

IO Command Set Attributes			
Bit[255:184]		Reserved	0x00
Bit[183:182]		Active Power Scale (APS)	0x0
Bit[181:179]		Reserved	0x0
Bit[178:176]		Active Power Workload (APW)	0x0
Bit[175:160]		Active Power (ACTP)	0x0
Bit[159:152]		Reserved	0x0
Bit[151:150]		Idle Power Scale (IPS)	0x0
Bit[149:144]		Reserved	0x0
Bit[143:128]		Idle Power (IDL P)	0x0
Bit[127:125]		Reserved	0x0
Bit[124:120]		Relative Write Latency (RWL)	0x3
Bit[119:117]		Reserved	0x0
Bit[116:112]		Relative Write Throughput (RWT)	0x3
Bit[111:109]		Reserved	0x0
Bit[108:104]		Relative Read Latency (RRL)	0x2
Bit[103:101]		Reserved	0x0
Bit[100:96]		Relative Read Throughput (RRT)	0x2
Bit[95:64]		Exit Latency (EXLAT)	0x0
Bit[63:32]		Entry Latency (ENLAT)	0x0
Bit[31:26]		Reserved	0x0
Bit[25]		Non-Operational State (NOPS)	0
Bit[24]		Max Power Scale (MPS)	0
Bit[23:16]		Reserved	0x0
Bit[15:0]		Maximum Power (MP)	0xB4
2207:2176	0	Power State 4 Descriptor (PSD4)	0x00
Bit[255:184]		Reserved	0x00
Bit[183:182]		Active Power Scale (APS)	0x0
Bit[181:179]		Reserved	0x0
Bit[178:176]		Active Power Workload (APW)	0x0
Bit[175:160]		Active Power (ACTP)	0x0
Bit[159:152]		Reserved	0x0
Bit[151:150]		Idle Power Scale (IPS)	0x0
Bit[149:144]		Reserved	0x0
Bit[143:128]		Idle Power (IDL P)	0x0
Bit[127:125]		Reserved	0x0
Bit[124:120]		Relative Write Latency (RWL)	0x4
Bit[119:117]		Reserved	0x0
Bit[116:112]		Relative Write Throughput (RWT)	0x4
Bit[111:109]		Reserved	0x0
Bit[108:104]		Relative Read Latency (RRL)	0x2
Bit[103:101]		Reserved	0x0
Bit[100:96]		Relative Read Throughput (RRT)	0x2
Bit[95:64]		Exit Latency (EXLAT)	0x0
Bit[63:32]		Entry Latency (ENLAT)	0x0
Bit[31:26]		Reserved	0x0

IO Command Set Attributes			
Bit[25]		Non-Operational State (NOPS)	0
Bit[24]		Max Power Scale (MPS)	0
Bit[23:16]		Reserved	0x0
Bit[15:0]		Maximum Power (MP)	0xB4
2239:2208	O	Power State 5 Descriptor (PSD5)	0x00
2271:2240	O	Power State 6 Descriptor (PSD6)	0x00
2303:2272	O	Power State 7 Descriptor (PSD7)	0x00
2335:2304	O	Power State 8 Descriptor (PSD8)	0x00
2367:2336	O	Power State 9 Descriptor (PSD9)	0x00
2399:2368	O	Power State 10 Descriptor (PSD10)	0x00
2431:2400	O	Power State 11 Descriptor (PSD11)	0x00
2463:2432	O	Power State 12 Descriptor (PSD12)	0x00
2495:2464	O	Power State 13 Descriptor (PSD13)	0x00
2527:2496	O	Power State 14 Descriptor (PSD14)	0x00
2559:2528	O	Power State 15 Descriptor (PSD15)	0x00
2591:2560	O	Power State 16 Descriptor (PSD16)	0x00
2623:2592	O	Power State 17 Descriptor (PSD17)	0x00
2655:2624	O	Power State 18 Descriptor (PSD18)	0x00
2687:2656	O	Power State 19 Descriptor (PSD19)	0x00
2719:2688	O	Power State 20 Descriptor (PSD20)	0x00
2751:2720	O	Power State 21 Descriptor (PSD21)	0x00
2783:2752	O	Power State 22 Descriptor (PSD22)	0x00
2815:2784	O	Power State 23 Descriptor (PSD23)	0x00
2847:2816	O	Power State 24 Descriptor (PSD24)	0x00
2879:2848	O	Power State 25 Descriptor (PSD25)	0x00
2911:2880	O	Power State 26 Descriptor (PSD26)	0x00
2943:2912	O	Power State 27 Descriptor (PSD27)	0x00
2975:2944	O	Power State 28 Descriptor (PSD28)	0x00
3007:2976	O	Power State 29 Descriptor (PSD29)	0x00
3039:3008	O	Power State 30 Descriptor (PSD30)	0x00
3071:3040	O	Power State 31 Descriptor (PSD31)	0x00
4095:3072	O	Vendor Specific.	0x00

Table 6-10 IO Vendor Specific

Vendor Specific			
4095:3072	O	Vendor Specific (VS)	Phison Reserved

NOTES:

* The OUI shall be a valid IEEE/RAC assigned identifier that may be registered at <http://standards.ieee.org/develop/regauth/oui/public.html>.

** Depends on the using of capacity

Table 6-11 Identify Namespace Data Structure & NVM Command Set Specific

Bytes	O/M	Description	Default Value
7:0	M	Namespace Size (NSZE)	TBD*

Bytes	O/M	Description	Default Value
15:8	M	Namespace Capacity (NCAP)	TBD*
23:16	M	Namespace Utilization (NUSE)	TBD*
24	M	Namespace Features (NSFEAT)	0x1E
25	M	Number of LBA Formats (NLBAF)	0x04
26	M	Formatted LBA Size (FLBAS)	0x00
27	M	Metadata Capabilities (MC)	0x03
28	M	End-to-end Data Protection Capabilities (DPC)	0x1B
29	M	End-to-end Data Protection Type Settings (DPS)	0x00
30	O	Namespace Multi-path I/O and Namespace Sharing Capabilities (NMIC)	0x01
31	O	Reservation Capabilities (RESCAP)	0xAB
32	O	Format Progress Indicator (FPI)	0x00
33	O	Deallocate Logical Block Features (DLFEAT):	0x19
35:34	O	Namespace Atomic Write Unit Normal (NAWUN)	0x0000
37:36	O	Namespace Atomic Write Unit Power Fail (NAWUPF)	0x0000
39:38	O	Namespace Atomic Compare & Write Unit (NACWU)	0x0000
41:40	O	Namespace Atomic Boundary Size Normal (NABSN)	0x0000
43:42	O	Namespace Atomic Boundary Offset (NABO)	0x0000
45:44	O	Namespace Atomic Boundary Size Power Fail (NABSPF)	0x0000
47:46	O	Namespace Optimal I/O Boundary (NOIOB):	0x0000
63:48	O	NVM Capacity (NVMCAP)	TBD*
65:64	O	Namespace Preferred Write Granularity (NPWG):	0x0000
67:66	O	Namespace Preferred Write Alignment (NPWA):	0x0000
69:68	O	Namespace Preferred Deallocate Granularity (NPDG):	0x0000
71:70	O	Namespace Preferred Deallocate Alignment (NPDA):	0x0000
73:72	O	Namespace Optimal Write Size (NOWS):	0x0000
91:74	-	Reserved	0x00
95:92	O	ANA Group Identifier (ANAGRPID):	0x00000000
98:96	-	Reserved	
99	O	Namespace Attributes (NSATTR):	0x00
101:100	O	NVM Set Identifier (NVMSETID):	0x0000
103:102	O	Endurance Group Identifier (NEDGID)	0x0000
119:104	O	Namespace Globally Unique Identifier (NGUID)	TBD**
127:120	O	IEEE Extended Unique Identifier (EUI64)	TBD**
131:128	M	LBA Format 0 Support (LBAF0)	0x02090000
135:132	O	LBA Format 1 Support (LBAF1)	0x00000000
139:136	O	LBA Format 2 Support (LBAF2)	0x00000000
143:140	O	LBA Format 3 Support (LBAF3)	0x00000000
147:144	O	LBA Format 4 Support (LBAF4)	0x00000000
151:148	O	LBA Format 5 Support (LBAF5)	0x00000000
155:152	O	LBA Format 6 Support (LBAF6)	0x00000000
159:156	O	LBA Format 7 Support (LBAF7)	0x00000000
163:160	O	LBA Format 8 Support (LBAF8)	0x00000000

Bytes	O/M	Description	Default Value
167:164	O	LBA Format 9 Support (LBAF9)	0x00000000
171:168	O	LBA Format 10 Support (LBAF10)	0x00000000
175:172	O	LBA Format 11 Support (LBAF11)	0x00000000
179:176	O	LBA Format 12 Support (LBAF12)	0x00000000
183:180	O	LBA Format 13 Support (LBAF13)	0x00000000
187:184	O	LBA Format 14 Support (LBAF14)	0x00000000
191:188	O	LBA Format 15 Support (LBAF15)	0x00000000
383:192		Reserved	0x00
4095:384	O	Vendor Specific (VS)	0x00

NOTES:

*According to IDEMA SPEC

** According to IEEE EUI-64 SPEC

Table 6-12 List of Identify Namespace Data Structure for Each Capacity

Capacity (GB)	Byte [7:0]: Namespace Size (NSZE)(Hex)	Byte [7:0]: Namespace Size (NSZE)(Dec)
960	6FC81AB0	960,197,124,096
1920	DF8FE2B0	1,920,383,410,176
3840	1BF1F72B0	3,840,755,982,336
1600	BA4D4AB0	1,600,321,314,816
3200	1749A42B0	3,200,631,791,616

6.3. SMART Attributes

Table 6-13 SMART Attributes (Log Identifier 02h)

Bytes Index	Bytes	Description
[0]	1	Critical Warning
[2:1]	2	Composite Temperature
[3]	1	Available Spare
[4]	1	Available Spare Threshold
[5]	1	Percentage Used
[31:6]	26	Reserved
[47:32]	16	Data Units Read
[63:48]	16	Data Units Written
[79:64]	16	Host Read Commands
[95:80]	16	Host Write Commands
[111:96]	16	Controller Busy Time
[127:112]	16	Power Cycles
[143:128]	16	Power On Hours
[159:144]	16	Unsafe Shutdowns
[175:160]	16	Media and Data Integrity Errors
[191:176]	16	Number of Error Information Log Entries
[195:192]	4	Warning Composite Temperature Time
[199:196]	4	Critical Composite Temperature Time
[201:200]	2	Temperature Sensor 1 (Current Temperature)
[203:202]	2	Temperature Sensor 2 (N/A)
[205:204]	2	Temperature Sensor 3 (N/A)
[207:206]	2	Temperature Sensor 4 (N/A)
[209:208]	2	Temperature Sensor 5 (N/A)
[211:210]	2	Temperature Sensor 6 (N/A)
[213:212]	2	Temperature Sensor 7 (N/A)
[215:214]	2	Temperature Sensor 8 (N/A)
[219:216]	4	Thermal Management Temperature 1 Transition Count
[223:220]	4	Thermal Management Temperature 2 Transition Count
[227:224]	4	Total Time For Thermal Management Temperature 1 (seconds)
[231:228]	4	Total Time For Thermal Management Temperature 2 (seconds)
[511:232]	280	Reserved

Table 6-14 SMART Attributes (Log Identifier C0h)

Bytes Index	Bytes	Description
[7:0]	8	Device Capacity
[15:8]	8	User Capacity
[23:16]	8	NAND Read
[31:24]	8	NAND Write
[39:32]	8	NAND Erase Sector
[47:40]	8	Wear Range Delta(%)
[55:48]	8	SSD Life Used Percent D3
[56]	1	WP Water Mark
[58:57]	2	Highest temperature

Bytes Index	Bytes	Description
[64:59]	8	Flash UNC Error Count
[68:65]	4	Data E3D Error
[72:69]	4	PHY Error Count
[76:73]	4	Total Bad Block Count
[80:77]	4	Total Early Bad Blcok Count
[84:81]	4	Total Later Bad Blcok Count
[88:85]	4	Read Fail Count
[92:89]	4	Program Fail Count
[96:93]	4	Erase Failure Count
[104:97]	8	System Table Copy Count
[112:105]	8	ReadMoveTableCnt
[116:113]	4	Data read retry count
[120:117]	4	RAID ECC retry count
[124:121]	4	RAID ECC failed count
[132:125]	8	Total Erase Count
[136:133]	4	D2/D3 Max Erase Cnount
[140:137]	4	D2/D3 Average Erase Count
[144:141]	4	D2/D3 Min Erase Count
[152:145]	8	Background read count
[156:153]	4	Host Write Uncorrectable Sector Count
[160:157]	4	PS3 Enter Success
[164:161]	4	PS4 Enter Success
[168:165]	4	Wear Leveling Count
[170:169]	2	Chip internal temperature
[172:171]	2	Thermal throttling
[174:173]	2	Thermal throttling time
[176:175]	8	FW Code Update Count
[177]	1	Current D1 SSD Life Used Percent
[511:178]	326	Reserved

Table 6-15 SMART Attributes (Log Identifier D2h)

Bytes Index	Bytes	Description
[7:0]	8	Device Capacity
[15:8]	8	User Capacity
[23:16]	8	NAND Read
[31:24]	8	NAND Write
[39:32]	8	NAND Erase Sector
[47:40]	8	Wear Range Delta(%)
[55:48]	8	SSD Life Used Percent D3
[56]	1	WP Water Mark
[58:57]	2	Highest temperature
[62:59]	4	Read Fail Count
[66:63]	4	Data E3D Error
[70:67]	4	PHY Error Count

Bytes Index	Bytes	Description
[74:71]	4	Total Bad Block Count
[78:75]	4	Total Early Bad Block Count
[82:79]	4	Total Later Bad Block Count
[86:83]	4	Read Fail Count
[90:87]	4	Program Fail Count
[94:91]	4	Erase Failure Count
[102:95]	8	System Table Copy Count
[110:96]	8	ReadMoveTableCnt
[114:111]	4	Data read retry count
[118:115]	4	RAID ECC retry count
[122:119]	4	RAID ECC failed count
[130:123]	8	Total Erase Count
[134:131]	4	D2/D3 Max Erase Count
[138:135]	4	D2/D3 Average Erase Count
[142:139]	4	D2/D3 Min Erase Count
[150:143]	8	Background read count (N/A)
[154:151]	4	Host Write Uncorrectable Sector Count
[158:155]	4	PS3 Enter Success (N/A)
[162:159]	4	PS4 Enter Success (N/A)
[166:163]	4	Wear Leveling Count
[168:167]	2	Chip internal temperature
[170:169]	2	Thermal throttling
[172:171]	2	Thermal throttling time
[180:173]	8	FW Code Update Count
[188:181]	8	Flash UNC Error Count
[192:189]	4	HB retry count
[196:193]	4	SB retry count
[511:197]	315	Reserved

7. PHYSICAL DIMENSION

Figure 7-1 shows the case mechanical information of Phison SSD PS5020-E20 X1 Series in the U.2 / U.3 2.5-inch 15mm form factor. All dimensions are in millimeters.

Figure 7-1 U.2 / U.3 2.5-inch 15mm Mechanical information

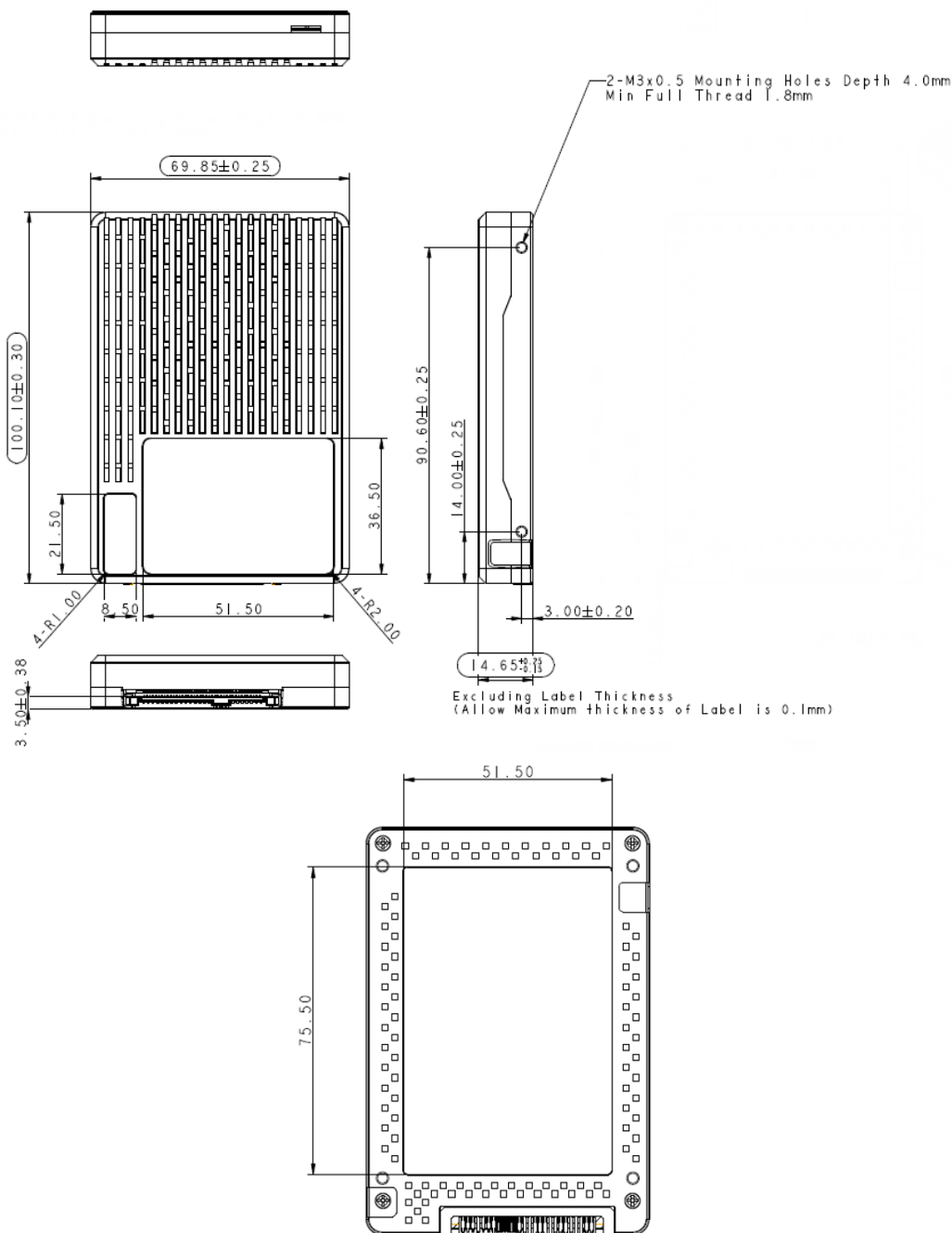


Table 7-1 U.2 / U.3 2.5-inch 15mm Length/Width/Height

	Nominal(mm)	Tolerance(mm)
Length	100.1	± 0.30
Width	69.85	± 0.25
Height	14.65	+0.25 / -0.15

Figure 7-2 shows the case mechanical information of Phison SSD PS5020-E20 X1 Series in the U.2 / U.3 2.5-inch 15mm form factor. All dimensions are in millimeters.

Figure 7-2 U.2 / U.3 2.5-inch 7mm Mechanical information

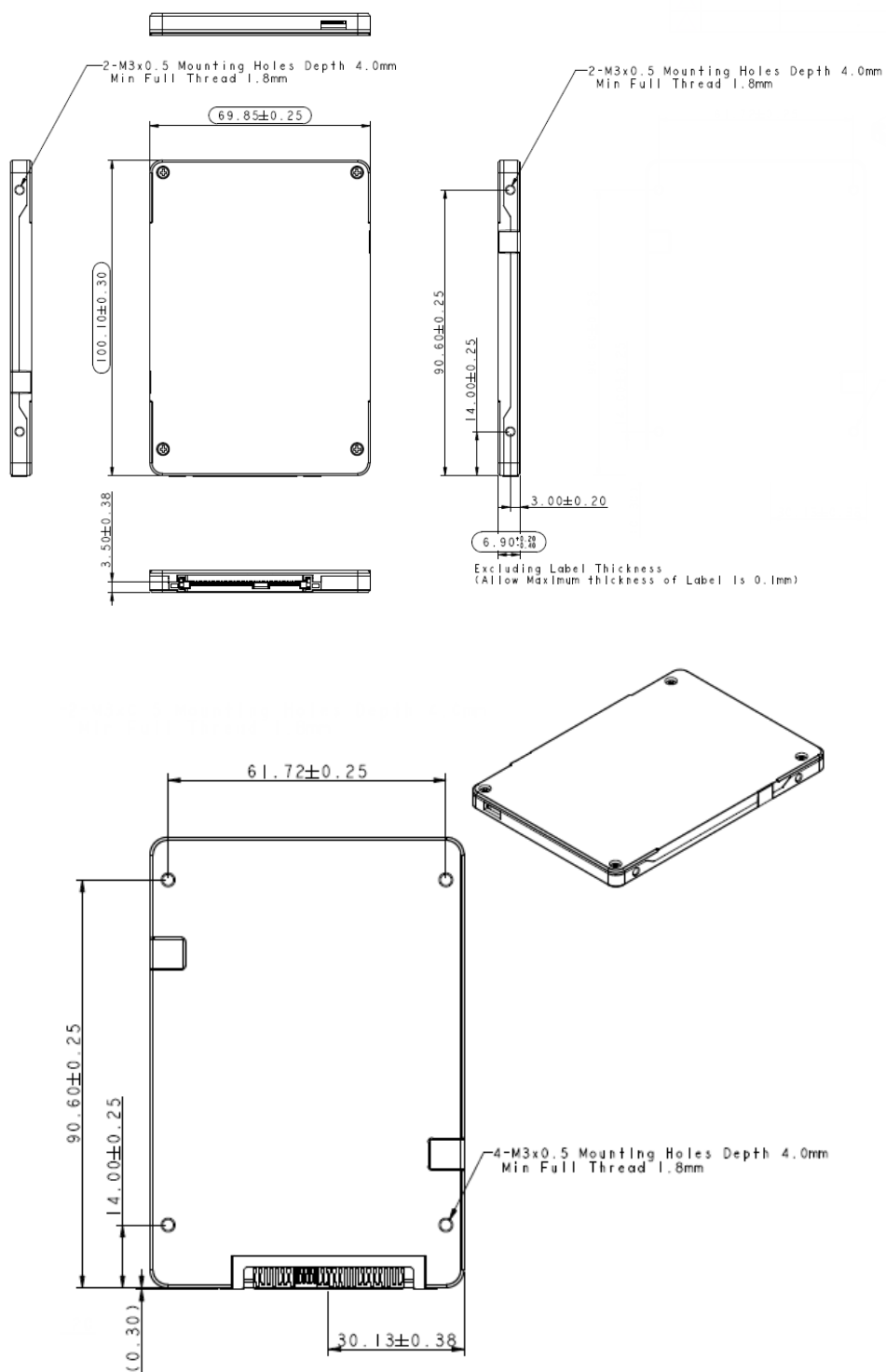


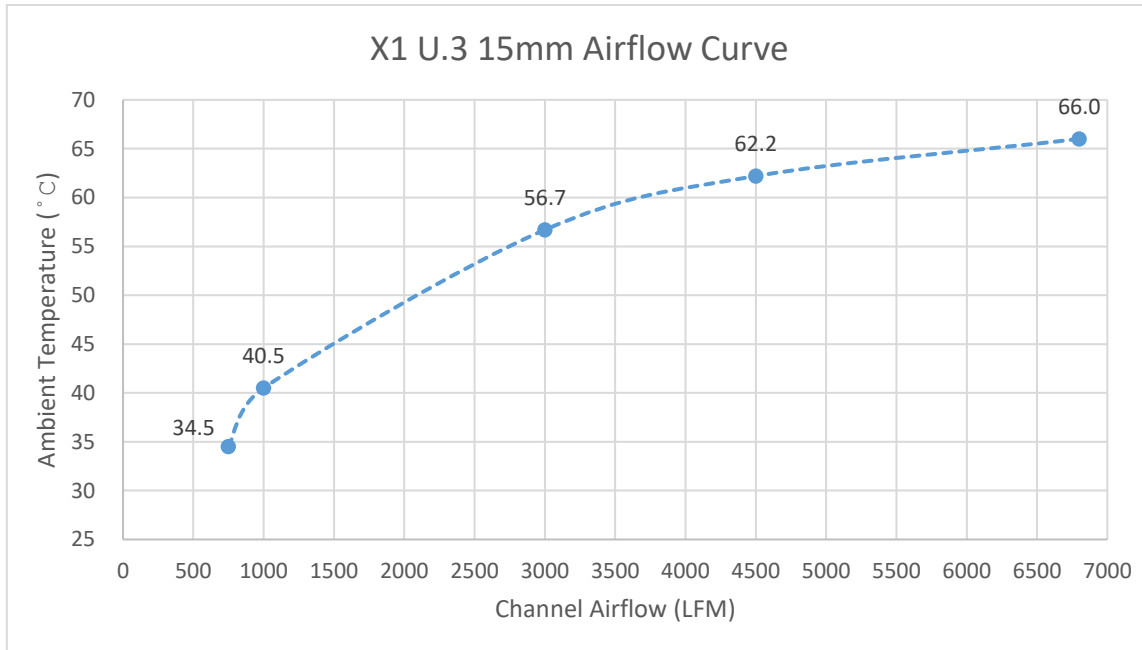
Table 7-2 U.2 / U.3 2.5-inch 7mm Length/Width/Height

	Nominal(mm)	Tolerance(mm)
Length	100.1	± 0.30
Width	69.85	± 0.25
Height	6.9	+0.20 / -0.40

8. AIR FLOW PROFILE

Figure 8-1 depicts the minimum airflow a U.3 15mm (8TB) needs to operate without triggering thermal throttling at ambient temperatures varied from 35°C to 65°C.

Figure 8-1 X1 U.3 15mm Airflow Curve



9. PERFORMANCE AND POWER SOP

The methodologies and platform used to obtain the power and performance numbers will be listed in the following sections. Again, performance and power may differ according to the flash configuration and platform used.

9.1. Performance Test Platform

Mother board: X570 AORUS MASTER Default string

CPU: AMD Ryzen 7 5800X 8-Core Processor

DRAM: DDR4 3200MHz 16GB

OS version: Windows 10 (10.0) Professional 64-bit

9.2. Performance methodologies

9.2.1. FIO Test procedure

- Secure erase - > no need format drive
 - 128K Seq. write/read
 1. Pre-con - 300% seq. write to full disk
 - a. IO Depth = 32
 - b. Number of jobs = 1
 2. Test script
 - a. IO Depth = 32
 - b. Number of Jobs= 1
 - c. Test duration: 300secs

9.2.2. IOPS consistency Test procedure

- Secure erase - > no need format drive
 - 4k random write/read
 1. Pre-con - 300% 4K random. write to full disk
 - a. IO Depth = 1
 - b. Number of jobs = 1
 2. Pre-con - 300% 4K random. write to full disk
 - c. IO Depth = 32
 - d. Number of jobs =1
 3. Pre-con - 300% 4K random. write to full disk
 - e. IO Depth = 64
 - f. Number of jobs = 8

9.2.3. Latency Test procedure

- Secure erase - > no need format drive
 - 4k random write/read
 1. Pre-con - 300% 4K random. write to full disk
 - a. IO Depth = 1
 - b. Number of jobs = 1
 2. Pre-con - 300% 4K random. write to full disk
 - a. IO Depth = 32
 - b. Number of jobs = 1

3. Pre-con - 300% 4K random. write to full disk
 - a. IO Depth = 64
 - b. Number of jobs = 8

9.2.4. QoS test procedure

- Secure erase - > no need format drive
 - 4k random write/read
 1. Pre-con - 300% 4K random. write to full disk
 - a. IO Depth = 1
 - b. Number of jobs = 1
 2. Pre-con - 300% 4K random. write to full disk
 - a. IO Depth = 32
 - b. Number of jobs = 1
 3. Pre-con - 300% 4K random. write to full disk
 - a. IO Depth = 64
 - b. Number of jobs = 8
- Data collection Procedure:
 1. Run entire test script one time.
 2. Run every condition in this script for 300 seconds
 3. Calculate average value for every condition.
 4. Get the average value, add some buffer and round down to the closest 10th
 5. Verify number with what was requested in PRD.

9.3. Power consumption Test Platform

Mother board: X570 AORUS MASTER Default string

CPU: AMD Ryzen 7 5800X 8-Core Processor

DRAM: DDR4 3200MHz 16GB

OS version: Ubuntu 16.04.3 LTS

9.4. Power consumption methodologies

9.4.1. Test Procedure

- 1T/2T/4T/8T device :
- Secure erase - > no need format drive -> Connect power board (Measure Current)
 - 2048k Seq. write/read
 1. Pre-con - 100% seq. write to full disk
 - a. IO Depth = 1024
 - b. Number of jobs = 1
 2. Test script (100% seq. write / 100% seq. read)
 - a. IO Depth = 1024
 - b. Number of Jobs= 1
 - c. Test duration: 900secs (for each performance)
 - 4k random write/read
 1. Test script
 - 100% ran. write / 100% ran. read / 70% ran. read + 30% ran write / 30% ran. read + 70% ran write
 - a. IO Depth = 256

- b. Number of Jobs= 12
 - c. Test duration: 900secs (for each performance)
- 16T device :
- Secure erase -> no need format drive -> Connect power board (Measure Current)
 - 128K Seq. write/read
 - 3. Pre-con - 100% seq. write to full disk
 - c. IO Depth = 32
 - d. Number of jobs = 1
 - 4. Test script (100% seq. write / 100% seq. read)
 - d. IO Depth = 32
 - e. Number of Jobs= 1
 - f. Test duration: 900secs (for each performance)
 - 4k random write/read
 - 2. Test script
 - 100% ran. write / 100% ran. read / 70% ran. read + 30% ran write / 30% ran. read + 70% ran write
 - d. IO Depth = 32
 - e. Number of Jobs= 8
 - f. Test duration: 900secs (for each performance)
- Data collection procedure – Max Average (10ms resolution)
 - a) Run entire test script one time.
 - b) Run every condition in this script
 - c) Calculate average value for every condition then choose maximum average
 - d) Note value for every condition
 - e) 6pcs sample for every capacity.
- Data collection procedure – Peak (1us resolution)
 - a) Run entire test script one time.
 - b) Run every condition in this script
 - c) Choose Maximum Value for every condition
 - d) Note the largest value as the Peak
 - e) 6pcs sample for every capacity.
- Data collection procedure – Power on
 - a) Run power on procedure until drive being ready to use.
 - b) Measure power to get Max Ave power and Max Peak power.
 - c) 6pcs sample for every capacity.
- Data collection procedure – Idle
 - a) After completing every condition, Idle for 30 secs.
 - b) Do nothing and measure power to get Max Ave Idle power and Max Peak power.
 - d) 6pcs sample for every capacity.

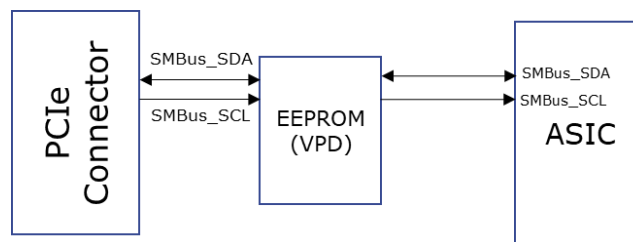
10. VITAL PRODUCT DATA

X1 U.2/U.3 devices can support Read and Write to Vital Product Data (VPD). Please refer to Figure 10-1 X1 U.3 PCIe SSD Controller Block Diagram for details on VPD Data Structure. VPD contains:

- Basic inventory information such as type and size of Enterprise PCIe SSD, manufacture, date, revision, and GUID.
- Power management data such as power level and power modes.
- Vendor specific data.

VPD is stored in a SMBus device with a slave address of 0xA6. VPD page can be read via SMBUS through address 0x53. Writes to the VPD page uses 0x53.

Figure 10-1 X1 U.3 PCIe SSD Controller Block Diagram



11. PCIE ID (APPENDIX)

Table 11-1 PCIe ID

ID Name	Description	U.3 15mm	PCIe Register Location	Identify Controller Location	Vital Product Data Location
Vendor ID (VID)	Vendor ID assigned by PCI-SIG	0x1BB1	PCI Header Offset 0x2	Identify Controller Data Structure Bytes 01:00	TBD
Device ID (DID)	Device ID assigned by vendor	0x5020	PCI Header Offset 0x0	N/A	TBD
Subsystem Vendor ID	Indicates Sub-system vendor ID	0x1987	PCI Header Offset 0x2C	Identify Controller Data Structure Bytes 03:02	TBD
Subsystem ID	Sub-system identifier	0x1987	PCI Header Offset 0x2E	N/A	TBD

12. PRODUCT WARRANTY POLICY

In the event the Product does not conform to the specification within Phison agreed warranty period and such inconformity is solely attributable to Phison's cause, Phison agrees at its discretion replace or repair the nonconforming Product. Notwithstanding the foregoing, the aforementioned warranty shall exclude the inconformity arising from, in relation to or associated with:

- (1) alternation, modification, improper use, misuse or excessive use of the Product;
- (2) failure to comply with Phison's instructions;
- (3) Phison's compliance with customer (including customer's suppliers, subcontractors or downstream customers) indicated instructions, technologies, designs, specifications, materials, components, parts;
- (4) combination of the Product with other materials, components, parts, goods, hardware, firmware or software not developed by Phison; or
- (5) other error or failure not solely attributable to Phison's cause (including without limitation, normal wear or tear, manufacturing or assembly wastage, improper operation, virus, unauthorized maintenance or repair).

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